

ABSTRACT OF THE DISCLOSURE

A crystal growth method, comprising the steps of: a) bringing a nitrogen material into a reaction vessel in which a mixed molten liquid comprising an alkaline metal and a group-III metal; and b) growing a crystal of a group-III nitride using the mixed molten liquid and the nitrogen material brought in by the step a) in the reaction vessel, wherein a provision is made such as to prevent a vapor of the alkaline metal from dispersing out of the reaction vessel.